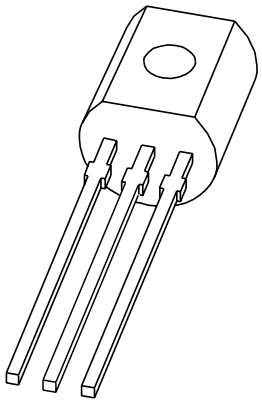
DATA SHEET



PSS9012 series
20 V PNP general purpose transistors

Product specification
Supersedes data of 2003 May 15

2004 Aug 10

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20 V PNP general purpose transistors PSS9012 series

FEATURES

- High power dissipation: 710 mW
- Low collector capacitance
- Low collector-emitter saturation voltage
- High current capability.

APPLICATIONS

- General purpose switching and amplification.

DESCRIPTION

PNP general purpose transistor in a SOT54 (TO-92) leaded plastic package. NPN complement: PSS9013 series.

MARKING

TYPE NUMBER	MARKING CODE
PSS9012G	S9012G
PSS9012H	S9012H

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	–20	V
I_C	collector current (DC)	–500	mA
I_{CM}	peak collector current	–1	A

PINNING

PIN	DESCRIPTION
1	collector
2	base
3	emitter

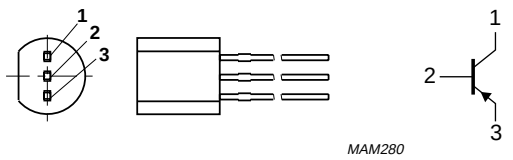


Fig.1 Simplified outline (SOT54; TO-92) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–40	V
V_{CEO}	collector-emitter voltage	open base	–	–20	V
V_{EBO}	emitter-base voltage	open collector	–	–5	V
I_C	collector current (DC)		–	–500	mA
I_{CM}	peak collector current		–	–1	A
I_{BM}	peak base current		–	–100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C; note 1	–	710	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Note

1. Device mounted on a FR4 printed-circuit board, single-sided copper, tinplated and standard footprint.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	in free air; note 1	175	K/W

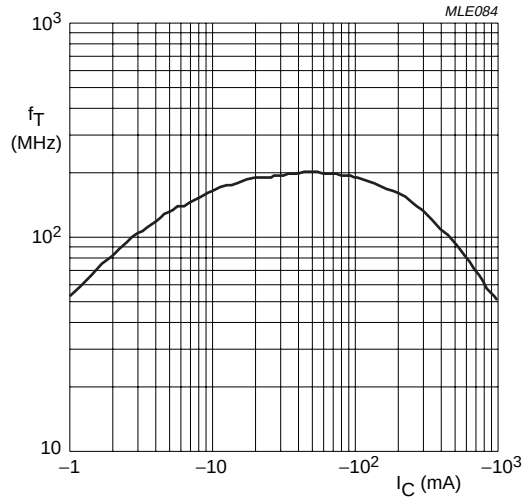
Note

1. Device mounted on a FR4 printed-circuit board, single-sided copper, tinplated and standard footprint.

CHARACTERISTICS

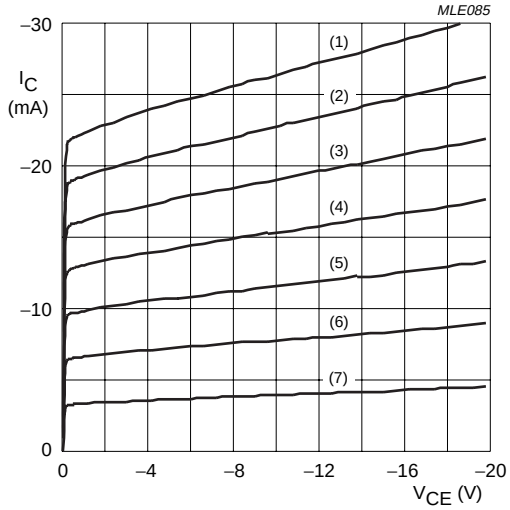
T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	V_{CB} = –35 V; I_E = 0	–	–	–100	nA
		V_{CB} = –35 V; I_E = 0; T_j = 150 °C	–	–	–50	µA
I_{EBO}	emitter-base cut-off current	V_{EB} = –5 V; I_C = 0	–	–	–100	nA
h_{FE}	DC current gain	V_{CE} = –1 V; I_C = –500 mA	40	–	–	
h_{FE}	DC current gain	V_{CE} = –1 V; I_C = –50 mA				
	PSS9012G		112	–	166	
	PSS9012H		144	–	202	
V_{CEsat}	collector-emitter saturation voltage	I_C = –100 mA; I_B = –10 mA	–	–60	–250	mV
		I_C = –500 mA; I_B = –50 mA	–	–230	–600	mV
V_{BEsat}	base-emitter saturation voltage	I_C = –500 mA; I_B = –50 mA	–	–1	–1.2	V
V_{BEon}	base-emitter turn on voltage	V_{CE} = –1 V; I_C = –100mA	–	–760	–1000	mV
C_c	collector capacitance	V_{CB} = –6 V; I_E = I_e = 0; f = 1 MHz	–	6	–	pF



V_{CE} = –6 V.

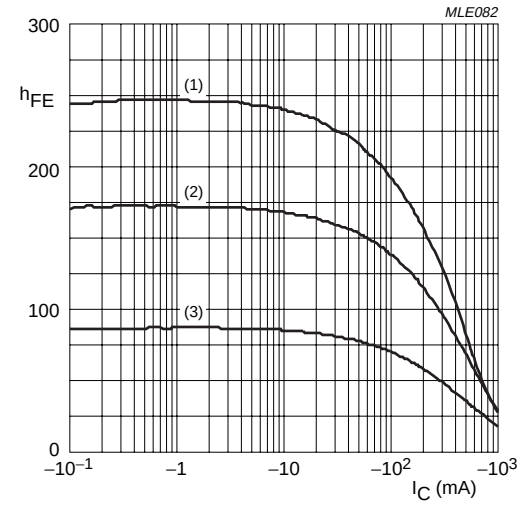
Fig.2 Transition frequency as a function of collector current; typical values.



T_{amb} = 25 °C.

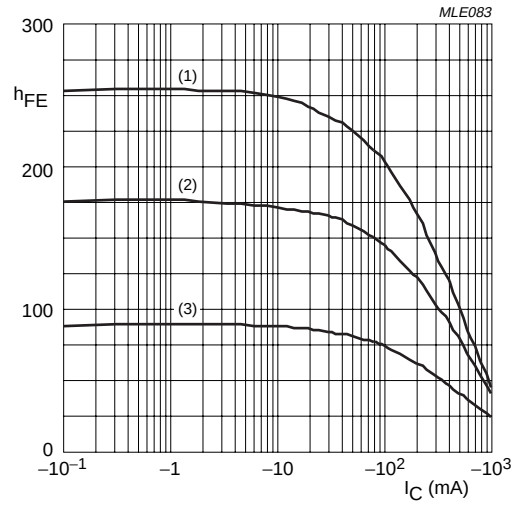
(1) I_B = –140 µA.
(2) I_B = –120 µA.
(3) I_B = –100 µA.
(4) I_B = –80 µA.
(5) I_B = –60 µA.
(6) I_B = –40 µA.
(7) I_B = –20 µA.

Fig.3 Collector current as a function of collector-emitter voltage; typical values.



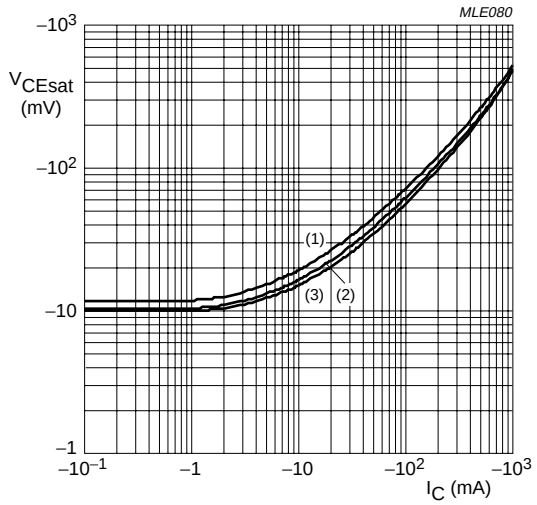
V_{CE} = –1 V.
(1) T_{amb} = 100 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = –55 °C.

Fig.4 DC current gain as a function of collector current; typical values.



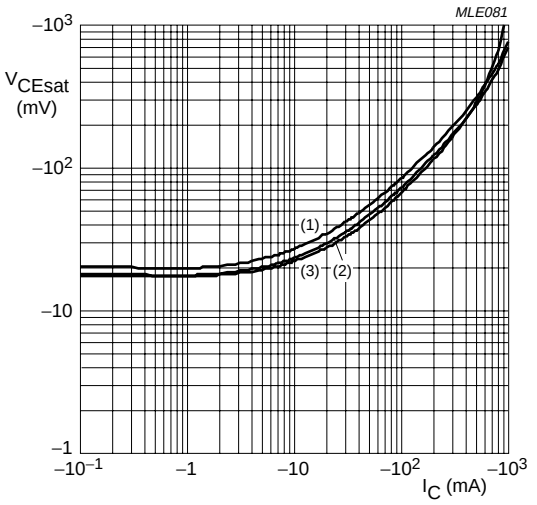
V_{CE} = –2 V.
(1) T_{amb} = 100 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = –55 °C.

Fig.5 DC current gain as a function of collector current; typical values.



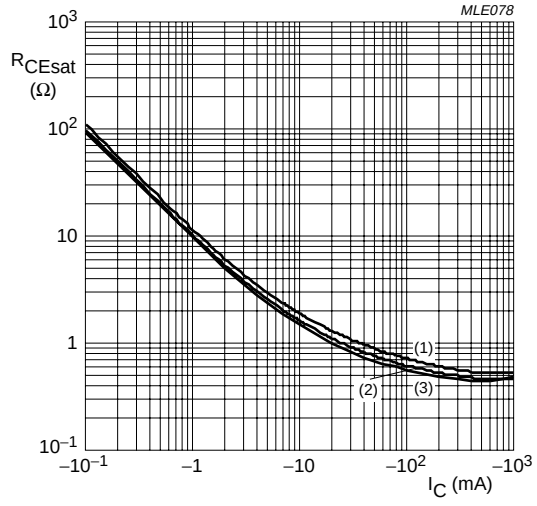
$I_C/I_B = 10$.
(1) $T_{amb} = 100$ °C.
(2) $T_{amb} = 25$ °C.
(3) $T_{amb} = -55$ °C.

Fig.6 Collector-emitter saturation voltage as a function of collector current; typical values.



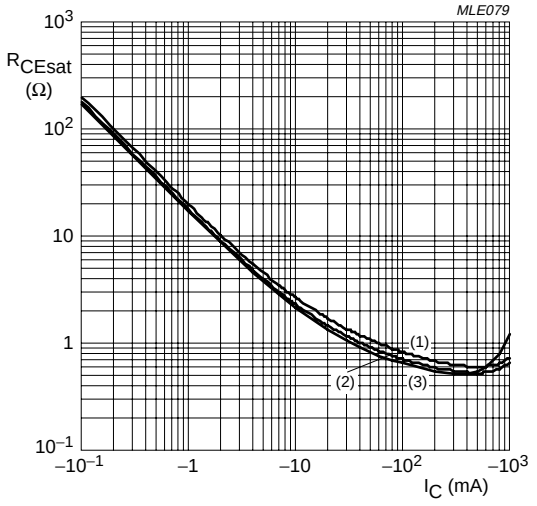
$I_C/I_B = 20$.
(1) $T_{amb} = 100$ °C.
(2) $T_{amb} = 25$ °C.
(3) $T_{amb} = -55$ °C.

Fig.7 Collector-emitter saturation voltage as a function of collector current; typical values.



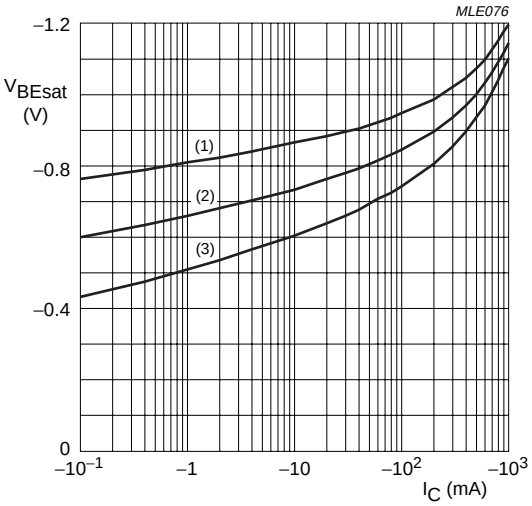
$I_C/I_B = 10$.
(1) $T_{amb} = 100$ °C.
(2) $T_{amb} = 25$ °C.
(3) $T_{amb} = -55$ °C.

Fig.8 Collector-emitter equivalent on-resistance as a function of collector current; typical values.



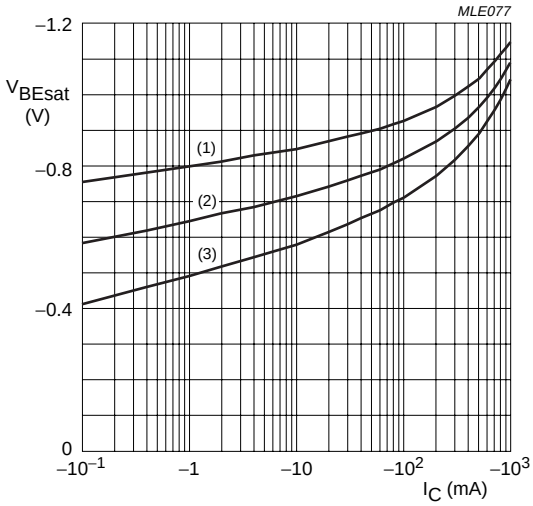
$I_C/I_B = 20$.
(1) $T_{amb} = 25$ °C.
(2) $T_{amb} = 100$ °C.
(3) $T_{amb} = -55$ °C.

Fig.9 Collector-emitter equivalent on-resistance as a function of collector current; typical values.



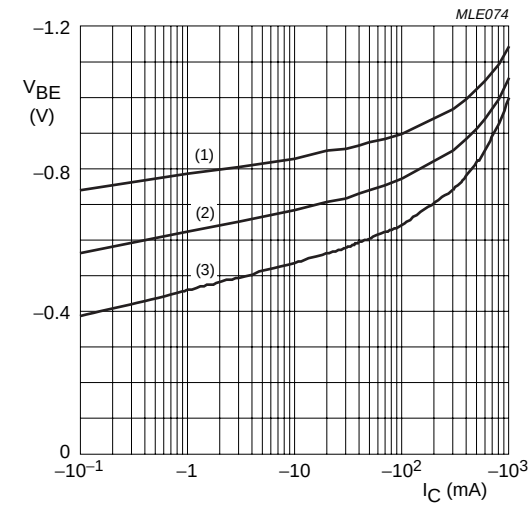
I_C/I_B = 10.
(1) T_{amb} = –55 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 100 °C.

Fig.10 Base-emitter saturation voltage as a function of collector current; typical values.



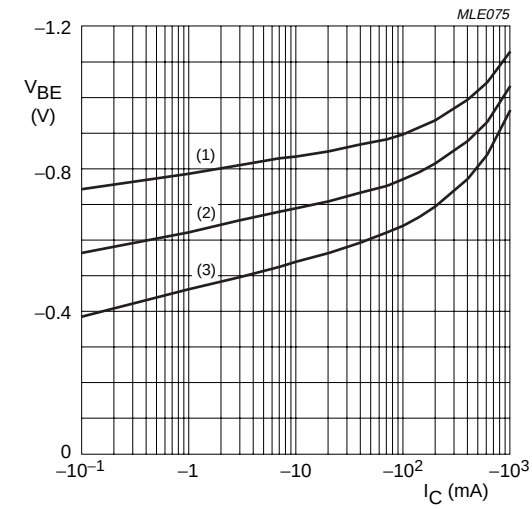
I_C/I_B = 20.
(1) T_{amb} = –55 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 100 °C.

Fig.11 Base-emitter saturation voltage as a function of collector current; typical values.



V_{CE} = –1 V.
(1) T_{amb} = –55 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 100 °C.

Fig.12 Base-emitter voltage as a function of collector current; typical values.

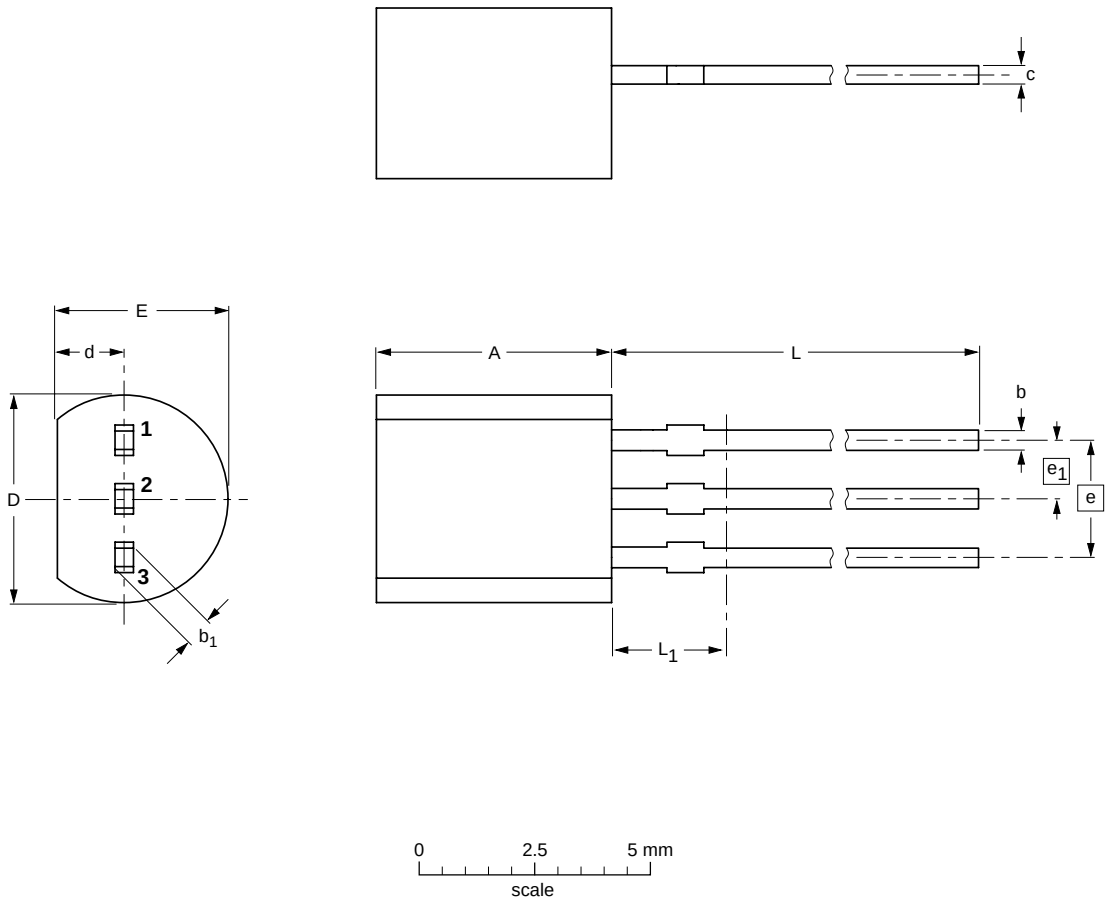


V_{CE} = –2 V.
(1) T_{amb} = –55 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 100 °C.

Fig.13 Base-emitter voltage as a function of collector current; typical values.

PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads **SOT54**



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b_1	c	D	d	E	e	e_1	L	L_1(1) max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT54		TO-92	SC-43A			~~97-02-28~~ 04-06-28

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS(1)	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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